Acta Crystallographica Section E Structure Reports Online

ISSN 1600-5368

Yongkwan Dong, Sangrok Kim and Hoseop Yun*

Department of Molecular Science and Technology, Ajou University, Suwon 442-749, South Korea

Correspondence e-mail: hsyun@ajou.ac.kr

Key indicators

Single-crystal X-ray study T = 150 KMean σ (Se–Ge) = 0.003 Å R factor = 0.056 wR factor = 0.145 Data-to-parameter ratio = 15.5

For details of how these key indicators were automatically derived from the article, see http://journals.iucr.org/e.

Reinvestigation of Hg₂GeSe₄ based on single-crystal data

Dimercury(II) germanium(IV) tetraselenide, Hg₂GeSe₄, adopts a cation-deficient diamond-like structure. It crystallizes in space group $I\overline{4}$ of the tetragonal system. The structure consists of tetrahedral [HgSe₄] and [GeSe₄] groups. These groups are interconnected by sharing common corners. The previous structure report on Hg₂GeSe₄ based on powder diffraction data [Parasyuk *et al.*, (2003). *J. Alloys Compd*, **351**, 135–144] is comparable with our results except for the absolute configuration determination. In the asymmetric unit, the site symmetries of the Hg and Ge atoms are $\overline{4}$.

Received 20 December 2004 Accepted 22 December 2004 Online 8 January 2005

Comment

The synthesis and crystal structure of Hg₂GeSe₄ have been reported, but with limited precision (Parasyuk et al., 2003). Single crystals of reasonable quality and size suitable for X-ray diffraction studies have not been obtained with traditional solid-state synthetic techniques. Consequently, the X-ray diffraction data have been collected from powders and structural analysis has been carried out by the Rietveld profile refinement technique. The previously reported crystal structure of Hg₂GeSe₄ has been refined in the non-centrosymmetric space group $I\overline{4}$ and the initial positional parameters were taken from cadmium thiogallate, CdGa₂S₄ (Krämer et al., 1983). We have used halide mixtures to prepare single crystals of metal chalcogenides, and this synthetic technique appears to be of general utility in preparing crystalline chalcogenides (Do & Yun, 1996; Kim et al., 1997). We describe here the synthesis and structural characterization of Hg₂GeSe₄ single crystals.

The general features of the structure of Hg_2GeSe_4 are the same as previously reported (Parasyuk *et al.*, 2003). Fig. 1



Figure 1

Interconnection of the tetrahedral [HgSe₄] and [GeSe₄] groups through sharing common Se atoms. Displacement ellipsoids are drawn at the 90% probability level. Symmetry codes are as given in Table 1.

© 2005 International Union of Crystallography Printed in Great Britain – all rights reserved



Figure 2 The structure of Hg2GeSe4, viewed down [100]. Large filled circles are Hg atoms, small filled circles are Ge atoms and open circles are Se atoms.

shows the interconnection of the [HgSe₄] and [GeSe₄] tetrahedra. There are two crystallographically independent mercury sites in the structure. The Hg-Se separations [2.658 (3) Å for Hg1–Se and 2.646 (3) Å for Hg2–Se] are in good agreement with those calculated from the covalent radii of Hg and Se (1.49 and 1.16 Å, respectively; radii taken from Webelements, 2004). While the bond distances between Hg and Se atoms are almost the same, the Hg2Se₄ tetrahedron is significantly distorted compared to the Hg1Se₄ tetrahedron. The Ge-Se distance [2.374 (2) Å] also agrees well with the sum of the covalent radii (Ge: 1.22 Å) and is comparable with those of other selenogermanates such as SrCu₂GeSe₄ [2.345 (5)–2.370 (4) Å; Tampier & Johrendt, 2001]. These tetrahedra are connected by sharing common corners, forming a three-dimensional network. As a result, the title compound belongs to the class of cation-deficient diamond-like structures, where one out of the four cationic sites is empty.

The cell parameters [a = 5.6786 (2) Å and c = 11.2579 (5) Å]and interatomic distances [Hg1-Se = 2.672 (4) Å, Hg2-Se =2.671 (4) Å and Ge–Se = 2.384 (4) Å] determined from the room temperature powder data are slightly larger than those of the present work performed at 150 K based on singlecrystal data. The difference is probably due simply to the temperature difference.

Experimental

Hg₂GeSe₄ was prepared by the reaction of HgSe, elemental Ge, and Se with the use of the reactive halide flux technique. A combination of HgSe (CERAC 99.8%), Ge powder (CERAC 99.5%) and Se powder (Aldrich 99.999%) was loaded in a quartz tube in a molar ratio of HgSe:Ge:Se = 1:1:5 and an ErCl₃/NaCl eutectic mixture was then added in a weight ratio of HgGeSe₆:ErCl₃/NaCl = 1:2. The tube was evacuated to 10^{-2} Torr, sealed, and heated gradually (50 K h⁻¹) to 1123 K in a tube furnace where it was kept for 24 h. The tube was cooled slowly to 373 K at a rate of 4 K h⁻¹ and quenched. Black shiny needle-shaped crystals up to 0.40 mm in length were found. The excess halides were removed with distilled water. The crystals are stable in air and water. Analysis of these crystals with the microprobe of an EDAX-equipped AMRAY 1200 C scanning electron microscope indicated the presence of Hg, Ge and Se. No other element was detected.

Crystal data

Hg₂GeSe₄ Mo $K\alpha$ radiation $M_r = 789.63$ Cell parameters from 22 Tetragonal, I4 reflections a = 5.6741 (17) Å $\theta = 12.0 - 14.5^{\circ}$ $\mu = 66.39 \text{ mm}^{-1}$ c = 11.249 (5) Å $V = 362.2 (2) \text{ Å}^3$ T = 150 (2) KZ = 2Needle, black $D_x = 7.241 \text{ Mg m}^{-3}$ $0.40\,\times\,0.02\,\times\,0.01~\text{mm}$

Data collection

MacScience MXC3 diffractometer $\omega/2\theta$ scans Absorption correction: analytical

(de Meulenaer & Tompa, 1965) $T_{\rm min}=0.220,\;T_{\rm max}=0.520$

288 measured reflections 263 independent reflections 260 reflections with $I > 2\sigma(I)$

Refinement

$(\Delta/\sigma)_{\rm max} < 0.001$
$\Delta \rho_{\rm max} = 3.24 \text{ e} \text{ Å}^{-3}$
$\Delta \rho_{\rm min} = -5.17 \text{ e } \text{\AA}^{-3}$
Extinction correction: SHELXL97
Extinction coefficient: 0.027 (4)
Absolute structure: Flack (1983), 38
Friedel pairs
Flack parameter = -0.01 (6)

 $R_{\rm int} = 0.066$

 $\theta_{\rm max} = 27.4^\circ$

 $h = 0 \rightarrow 7$

 $k = 0 \rightarrow 7$

 $l = 0 \rightarrow 14$

2 standard reflections

every 100 reflections

intensity decay: 0.5%

Table 1

Selected geometric parameters (Å, °).

Hg1-Se ⁱ	2.658(3)	Ge-Se ⁱⁱⁱ	2.374 (2)
Ng2-Se	2.040 (3)	Se ⁱⁱ _Hg2_Se ^v	104 49 (5)
Se ⁱ -Hg1-Se ^v	111.86 (11)	Se ⁱⁱⁱ -Ge-Se ^{vii}	102.34 (13)
Se ⁿ -Hg2-Se ^{vi}	119.97 (12)	Se ^m -Ge-Se ^{vm}	113.15 (7)
Symmetry codes: (i) y , $1 - x$, $1 - z$; (v) $\frac{1}{2}$	$x - \frac{1}{2}, \frac{1}{2} + y, z - \frac{1}{2};$ (ii) $-x, \frac{1}{2} - y, z - \frac{1}{2};$ (vi)	$\frac{1}{2} - y, x - \frac{1}{2}, \frac{3}{2} - z;$ (iii) 1 $y - \frac{1}{2}, \frac{1}{2} - x, \frac{3}{2} - z;$ (vii)	-x, 1-y, z; (iv) x-1, y, z; (viii)
$y = \frac{1}{2}, \frac{3}{2} = x, \frac{3}{2} = z.$. 2 2	2.2.2	

The absolute structure for this particular crystal was found to be the opposite of that represented by the published coordinates from the previous powder study (Parasyuk *et al.*, 2003) gave a value of x =0.85(9) for the Flack (1983) parameter (wR2 = 0.1913), which suggests that the absolute structure may not be correct. Refinement of the inverse structure which is in agreement with the selected setting of this work leads to x = -0.01 (6) and significantly improved the reliability factor (wR2 = 0.1449). The highest residual electron density is 2.32 Å from the Hg1 site and the deepest hole is 0.95 Å from the Se site.

Data collection: MXC3 Diffractometer Control Software (MacScience, 1994); cell refinement: MXC3 Diffractometer Control Software; data reduction: MXC3 Diffractometer Control Software; program(s) used to solve structure: SHELXS86 (Sheldrick, 1985); program(s) used to refine structure: *SHELXL*97 (Sheldrick, 1997); molecular graphics: *ORTEP-3* (Farrugia, 1997); software used to prepare material for publication: *WinGX* (Farrugia, 1999).

This research was supported by the Korean Research Foundation (KRF 2000-042-D00054).

References

Do, J. & Yun, H. (1996). Inorg. Chem. 35, 3729–3730.
Farrugia, L. J. (1997). J. Appl. Cryst. 30, 565.
Farrugia, L. J. (1999). J. Appl. Cryst. 32, 837–838.

- Flack, H. D. (1983). Acta Cryst. A39, 876-881.
- Kim, C, Yun, H., Lee, Y., Shin, H. & Liou, K. (1997). J. Solid State Chem. 132, 389–393.
- Krämer, V., Frick, B. & Siebert, D. (1983). Z. Kristallogr. 165, 151-157.
- MacScience (1994). MXC3 Diffractometer Control Software. MacScience Corporation, Tokyo, Japan.
- Meulenaer, J. de & Tompa, H. (1965). Acta Cryst. 19, 1014-1018.
- Parasyuk, O., Gulay, L., Romanyuk, Y., Olekseyuk, I. & Piskach, L. (2003). J. Alloys Compd, 351, 135–144.
- Sheldrick, G. M. (1985). SHELXS86. Crystallographic Computing 3, edited by G. M. Sheldrick, C. Krüger and R. Goddard, pp. 175–189. Oxford University Press.
- Sheldrick, G. M. (1997). SHELXL97. University of Göttingen, Germany.
- Tampier, M. & Johrendt, D. (2001). Z. Anorg. Allg. Chem. 627, 312–320.
- Webelements (2004). URL: http://www.webelements.com/